KERSEMI ELECTRONIC CO.,LTD.

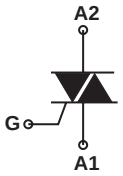
BTA20 BW/CW
BTB20 BW/CW

SNUBBERLESS TRIACS

FEATURES

- High commutation: (dI/dt)c > 18A/ms without snubber
- High surge current: I_{TSM} = 200A
- V_{DRM} up to 800V
- BTA Family:
  Insulating voltage = $2500V_{(RMS)}$
  (UL recognized: E81734)

TO-220AB



DESCRIPTION

The BTA/BTB20 BW/CW triac family are high performance glass passivated chips technology.
The SNUBBERLESS™ concept offer suppression of RC network and it is suitable for application such as phase control and static switching on inductive or resistive load.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (360° conduction angle)	BTA	Tc = 70°C	20	A
		BTB	Tc = 90°C		
I_{TSM}	Non repetitive surge peak on-state current (Tj initial = 25°C)		tp = 8.3ms	210	A
			tp = 10ms	200	
I^2t	I^2t value		tp = 10ms	200	A^2s
dI/dt	Critical rate of rise of on-state current Gate supply: I_G = 500mA dI_G/dt = 1A/µs		Repetitive F = 50Hz	20	A/µs
			Non repetitive	100	
Tstg Tj	Storage and operating junction temperature range			-40 to +150 -40 to +125	°C
Tl	Maximum lead soldering temperature during 10s at 4.5mm from case			260	°C

Symbol	Parameter	BTA/BTB20-...BW/CW		Unit
		600	700	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Tj = 125°C	600	700	V

THERMAL RESISTANCE

Symbol	Parameter		Value	Unit
Rth (j-a)	Junction to ambient		60	°C/W
Rth (j-c) DC	Junction to case for DC	BTA	2.8	°C/W
		BTB	1.7	
Rth (j-c) AC	Junction to case for 360° conduction angle (F = 50Hz)	BTA	2.1	°C/W
		BTB	1.3	

GATE CHARACTERISTICS (maximum values)

$P_{G(AV)}$ = 1W P_{GM} = 10W (tp = 20µs) I_{GM} = 4A (tp = 20µs) V_{GM} = 16V (tp = 20µs)

ELECTRICAL CHARACTERISTICS

Symbol	Test conditions		Quadrant		BTA / BTB20		Unit
					BW	CW	
I_{GT}	V_D = 12V (DC) R_L = 33Ω	Tj = 25°C	I - II - III	MIN.	2	1	mA
				MAX.	50	35	
V_{GT}	V_D = 12V (DC) R_L = 33Ω	Tj = 25°C	I - II - III	MAX.	1.5		V
V_{GD}	V_D = V_{DRM} R_L = 3.3kΩ	Tj =125°C	I - II - III	MIN.	0.2		V
tgt	V_D = V_{DRM} I_G = 500mA dI_G/dt = 3A/µs	Tj = 25°C	I - II - III	TYP.	2		µs
I_L	I_G = 1.2I_{GT}	Tj = 25°C	I - III	TYP.	50	-	mA
			II		90	-	
			I - II - III	MAX.	-	80	
I_H*	I_T = 500mA Gate open	Tj = 25°C		MAX.	75	50	mA
V_{TM} *	I_{TM} = 28A tp = 380µs	Tj = 25°C		MAX.	1.70		V
I_{DRM} I_{RRM}	V_{DRM} rated V_{RRM} rated	Tj = 25°C		MAX.	0.01		mA
		Tj = 125°C		MAX.	3		
dV/dt *	Linear slope up to V_D = 67% V_{DRM} gate open	Tj = 125°C		TYP.	750	500	V/µs
				MIN.	500	250	
(dI/dt)c*	Without snubber	Tj = 125°C		TYP.	36	22	A/ms
				MIN.	18	11	

* For either polarity of electrode A_2 voltage with reference to electrode A_1

PRODUCT INFORMATION

Package	$I_{T(RMS)}$	V_{DRM} / V_{RRM}	Sensitivity Specification	
	A	V	BW	CW
BTA (Insulated)	20	600	X	X
		700	X	X
BTB (Uninsulated)		600		X

ORDERING INFORMATION

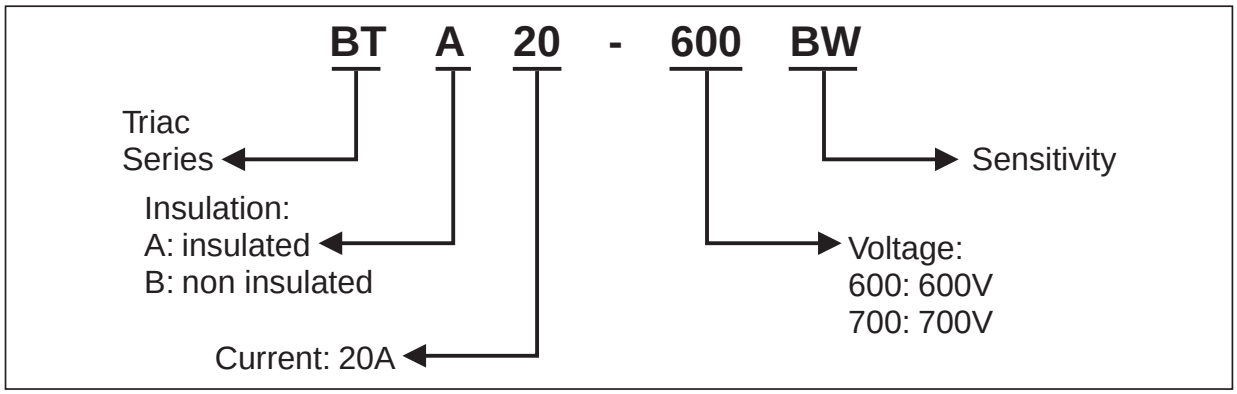


Fig. 1: Maximum RMS power dissipation versus RMS on-state current (F = 50Hz).(Curves are cut off by (dI/dt)c limitation)

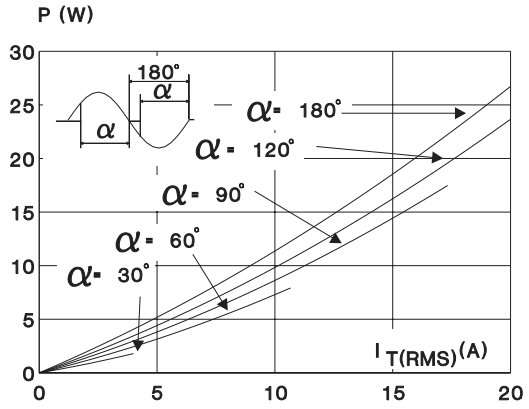


Fig. 2: Correlation between maximum RMS power dissipation and maximum allowable temperatures (Tamb and Tcase) for different thermal resistances heatsink + contact (BTA).

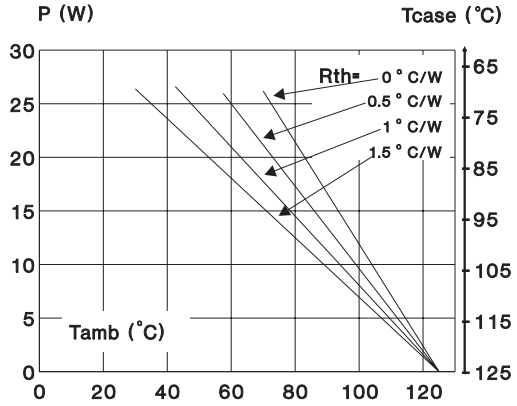


Fig. 3: Correlation between maximum RMS power dissipation and maximum allowable temperatures (Tamb and Tcase) for different thermal resistances heatsink + contact (BTB).

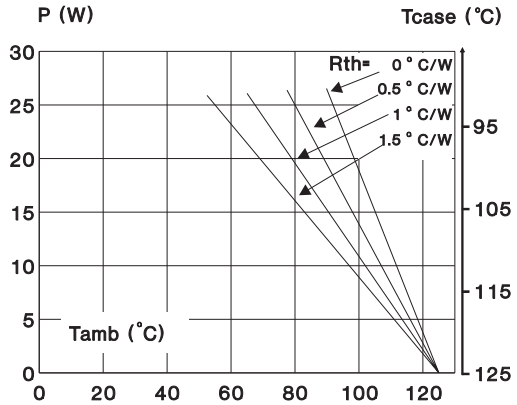


Fig. 4: RMS on-state current versus case temperature.

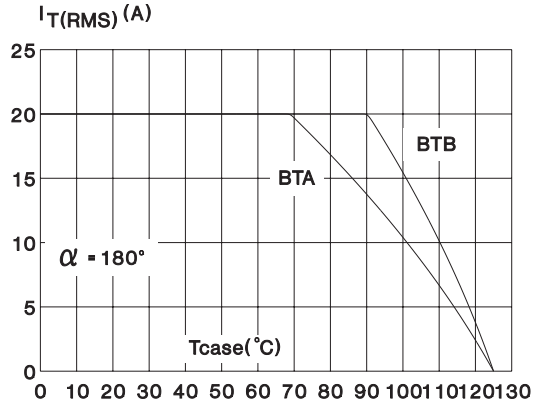


Fig. 5: Relative variation of thermal impedance versus pulse duration.

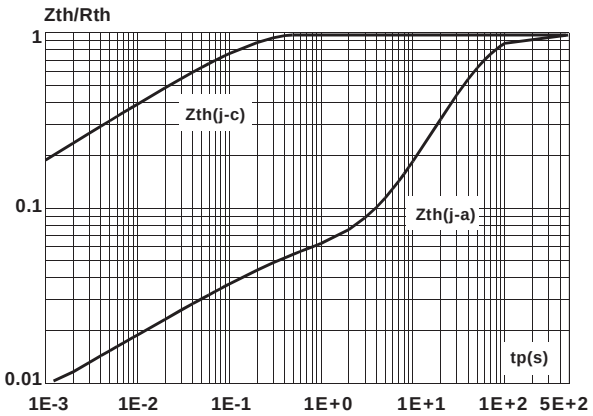


Fig. 6: Relative variation of gate trigger current and holding current versus junction temperature.

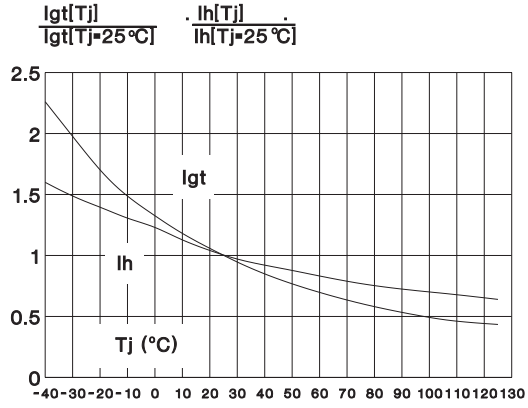


Fig. 7: Non repetitive surge peak on-state current versus number of cycles.

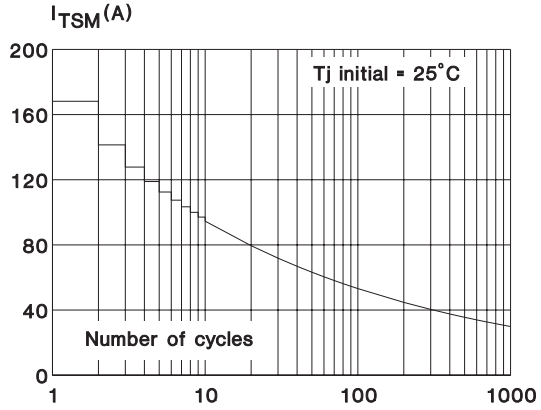


Fig. 8: Non repetitive surge peak on-state current for a sinusoidal pulse with width: t ≤ 10ms, and corresponding value of I^2t.

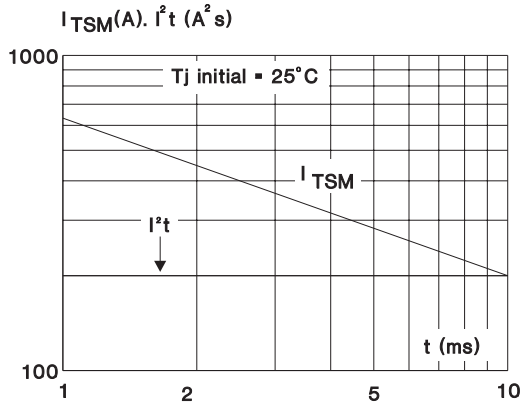


Fig. 9: On-state characteristics (maximum values).